

What is claimed is:

1. A wafer observation method for enlarging and observing, with a pattern observation device, a plurality of wafer pattern control points formed on a wafer based on CAD data, wherein

the plurality of control points are determined by analysis of the CAD data, a set of observation coordination data are acquired in accordance with the determined plurality of control points, the CAD data are referenced to carry out positional navigation in accordance with the set of observation coordinate data, and the determined plurality of control points of the wafer pattern are sequentially observed.

2. The wafer observation method of claim 1, wherein determination of the plurality of control points is carried out using lithography simulation, device simulation, process simulation, etching simulation, or a CAD pattern density analysis method.

3. The wafer observation method of claim 1, wherein the positional navigation method is realized as a CAD navigation method that performs observational positioning of the pattern observation device to a low magnification factor so that observation centers of the control points are placed in an observation field of view to acquire wafer pattern low magnification factor pattern image data, calculates an offset amount between the observation centers and centers of the observation field of view from the low magnification factor pattern image data and CAD graphics data corresponding to the low magnification factor pattern image data, and performs relative positional control of the wafer based on this offset amount data so that the centers of observation are aligned with the centers of the observation field of view.

